SiT9365

Standard Frequency Ultra-low Jitter Differential Oscillator

Description

The SiT9365 is a differential MEMS XO supporting standard frequencies between 25 MHz and 325 MHz, and engineered for low-jitter applications. Utilizing SiTime's unique DualMEMS® temperature sensing and TurboCompensation® technology, the SiT9365 delivers exceptional dynamic performance by providing resistance to airflow, thermal gradients, shock and vibration. This device also integrates multiple on-chip regulators to filter power supply noise, eliminating the need for a dedicated external LDO.

The SiT9365 can be factory programmed for specific combinations of frequency, stability, voltage, and output signaling. Programmability enables designers to optimize clock configurations while eliminating long lead times and customization costs associated with quartz devices where each frequency is custom built.

Standard frequencies and programmability makes this device ideal for telecom, networking, and industrial applications that require a variety of frequencies and operate in noisy environments.

Refer to Manufacturing Notes for proper reflow profile, tape and reel dimension, and other manufacturing related information.

Features

- 32 standard frequencies from 25 MHz to 325 MHz (For additional frequencies, refer to SiT9366 and SiT9367 datasheets)
- LVPECL, Low-swing LVPECL, LVDS and HCSL output signaling
- 0.1 ps RMS phase jitter (random) for Ethernet applications
- Frequency stability as low as ±10 ppm
- Wide temperature ranges from -40°C to 105°C
- Industry-standard packages: 3.2 x 2.5 mm^2, 7.0 x 5.0 mm^2 and 5.0 x 3.2 mm^2 package

Applications

- 10/40/100 Gbps Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers

Block Diagram

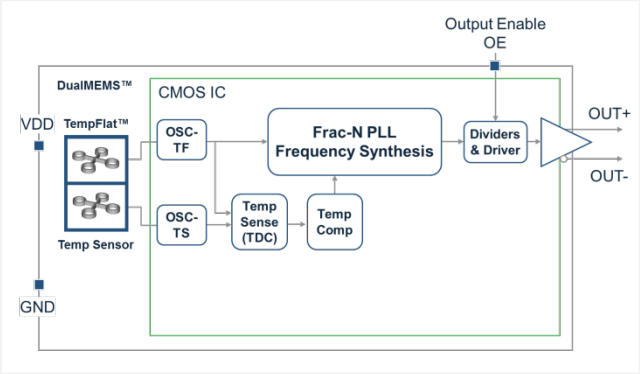

Figure 1. SiT9365 Block Diagram

Package Pinout

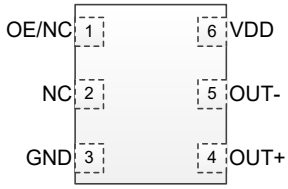

Figure 2. Pin Assignments (Top view)
(Refer to Table 7 for Pin Descriptions)

Ordering Information

SiT9365AC-1B2-33E125.000000T

Part Family
"SiT9365"

Revision Letter
"A" is the revision of Silicon

Temperature Range
"C": Extended Commercial, -20 to 70°C
"I": Industrial, -40 to 85°C
"B": -40 to 95 °C
"E": Extended Industrial, -40 to 105°C

Signalling Type
"1": LVPECL
"2": LVDS
"4": HCSL
"5": Low-swing LVPECL

Package Size
"B": 3.2 x 2.5 mm
"C": 5.0 x 3.2 mm with center pad
"E": 7.0 x 5.0 mm with center pad

Frequency Stability
"F": ±10 ppm
"1": ±20 ppm
"2": ±25 ppm
"3": ±50 ppm

Packaging
"T", "Y", "D" or "E"
Refer to table below for packing method
Leave Blank for Bulk[1]

Frequency
See supported frequency list below

Feature Pin
"N": No Connect
"E": Output Enable

Voltage Supply
"25": 2.5 V ±10%
"28": 2.8 V ±10%
"30": 3.0 V ±10%
"33": 3.3 V ±10%

Notes:
1. Bulk is available for sampling only.

Table 1. Supported Frequencies

25.000000 MHz	30.720000 MHz	50.000000 MHz	53.125000 MHz	61.440000 MHz	62.500000 MHz	74.175824 MHz	74.250000 MHz
75.000000 MHz	77.760000 MHz	98.304000 MHz	100.000000 MHz	106.250000 MHz	122.880000 MHz	125.000000 MHz	133.333333 MHz
148.351648 MHz	150.000000 MHz	153.600000 MHz	155.520000 MHz	156.250000 MHz	159.375000 MHz	160.000000 MHz	161.132813 MHz
166.666666 MHz	168.040678 MHz	200.000000 MHz	212.500000 MHz	250.000000 MHz	300.000000 MHz	322.265625 MHz	325.000000 MHz

Table 2. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	—	—	—	—	T	Y
5.0 x 3.2			T	Y		
3.2 x 2.5	D	E			—	—

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Electrical Characteristics

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination shown in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

Table 3. Electrical Characteristics – Common to LVPECL, Low-swing LVPECL, LVDS and HCSL (All temperature ranges)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Output Frequency Range	f	32 standard frequencies between 25 MHz and 325.000000 MHz			MHz	
Frequency Stability						
Frequency Stability	F_stab	-10	–	+10	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations
		-20	–	+20	ppm	
		-25	–	+25	ppm	
		-50	–	+50	ppm	
First Year Aging	F_1y	-0.7	±0.4	+0.7	ppm	At 85°C
5 Year Aging	F_5y	-1.1	±0.7	+1.1	ppm	At 85°C
10 Year Aging	F_10y	-1.3	±0.8	+1.3	ppm	At 85°C
20 Year Aging	F_20y	-1.5	±1.0	+1.5	ppm	At 85°C
Temperature Range						
Operating Temperature Range	T_use	-20	–	+70	°C	Extended Commercial
		-40	–	+85	°C	Industrial
		-40	–	+95	°C	
		-40	–	+105	°C	Extended Industrial
Supply Voltage						
Supply Voltage	Vdd	2.97	3.30	3.63	V	
		2.70	3.00	3.30	V	
		2.52	2.80	3.08	V	
		2.25	2.50	2.75	V	
Input Characteristics						
Input Voltage High	VIH	70%	–	–	Vdd	Pin 1, OE
Input Voltage Low	VIL	–	–	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	–	100	–	kΩ	Pin 1, OE logic high or logic low
Output Characteristics						
Duty Cycle	DC	45	–	55	%	
Startup and OE Timing						
Startup Time	T_start	–	–	3.0	ms	Measured from the time Vdd reaches its rated minimum value.
OE Enable/Disable Time	T_oe	–	–	3.8	µs	f = 156.25 MHz. Measured from the time OE pin reaches rated VIH and VIL to the time clock pins reach 90% of swing and high-Z. See Figure 8 and Figure 9.

Table 4. Electrical Characteristics – LVPECL, Low-swing LVPECL

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	89	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Maximum Output Current	I_driver	–	–	30	mA	Maximum average current drawn from OUT+ or OUT-
Output Characteristics for LVPECL						
Output High Voltage	VOH	Vdd-1.1	–	Vdd-0.7	V	See Figure 4
Output Low Voltage	VOL	Vdd-1.9	–	Vdd-1.5	V	See Figure 4
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 5
Rise/Fall Time	Tr, Tf	–	225	290	ps	20% to 80%. See Figure 5
Output Characteristics for Low-swing LVPECL						
Output High Voltage	VOH	Vdd-1.2	–	Vdd-0.75	V	See Figure 4
Output Low Voltage	VOL	Vdd-1.8	–	Vdd-1.25	V	See Figure 4
Output Differential Voltage Swing	V_Swing	0.4	1	1.2	V	Output frequency less than or equal to 220 MHz, See Figure 5
		0.4	1	1.6	V	Output frequency greater than 220 MHz, See Figure 5
Rise/Fall Time	Tr, Tf	–	225	290	ps	20% to 80%. See Figure 5
Jitter – 7.0 x 5.0 mm Package						
RMS Period Jitter[2]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	–	0.225	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.225	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
Jitter – 5.0 x 3.2 mm and 3.2 x 2.5 mm Packages						
RMS Period Jitter[2]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V
RMS Phase Jitter (random)		–	0.225	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.225	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.

Notes:

2. Measured according to JESD65B.

Table 5. Electrical Characteristics – LVDS

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	79	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Output Characteristics						
Differential Output Voltage	VOD	300	–	450	mV	See Figure 6
Delta VOD	ΔVOD	–	–	50	mV	See Figure 6
Offset Voltage	VOS	1.125	–	1.375	V	See Figure 6
Delta VOS	ΔVOS	–	–	50	mV	See Figure 6
Rise/Fall Time	Tr, Tf	–	400	470	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%. See Figure 7
Jitter – 7.0 x 5.0 mm Package						
RMS Period Jitter[3]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	–	0.215	0.265	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.215	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
Jitter – 5.0 x 3.2 and 3.2 x 2.5 mm Packages						
RMS Period Jitter[1]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	–	0.235	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.235	0.320	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.

Notes:

3. Measured according to JESD65B.

Table 6. Electrical Characteristics – HCSL

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	89	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Maximum Output Current	I_driver	–	–	35	mA	Maximum average current drawn from OUT+ or OUT-
Output Characteristics						
Output High Voltage	VOH	0.60	–	0.90	V	See Figure 4
Output Low Voltage	VOL	-0.05	–	0.08	V	See Figure 4
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.80	V	See Figure 5
Rise/Fall Time	Tr, Tf	–	360	465	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%. See Figure 5
Jitter – 7.0 x 5.0 mm Package						
RMS Period Jitter[4]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	–	0.220	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.220	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
Jitter – 5.0 x 3.2 and 3.2 x 2.5 mm Packages						
RMS Period Jitter[4]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	–	0.230	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70ºC and -40 to 85ºC
		–	0.230	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95ºC and -40 to 105ºC
		–	0.1	–	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.

Notes:

4. Measured according to JESD65B.

Table 7. Pin Description

Pin	Map	Functionality	
1	OE/NC	Output Enable (OE)	H[5]: specified frequency output L: output is high impedance
		Non Connect (NC)	H or L or Open: No effect on output frequency or other device functions
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation
3	GND	Power	VDD Power Supply Ground
4	OUT+	Output	Oscillator output
5	OUT-	Output	Complementary oscillator output
6	VDD	Power	Power supply voltage[6]

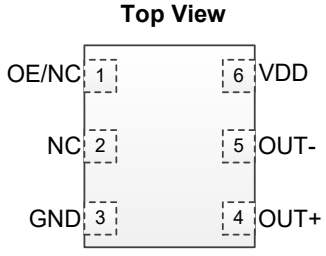


Figure 3. Pin Assignments

Notes:

5. In OE mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven.
6. A capacitor of value 0.1 µF or higher between VDD and GND is required. An additional 10 µF capacitor between VDD and GND is required for the best phase jitter performance.

Table 8. Absolute Maximum Ratings

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part.
Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Vdd	-0.5	4.0	V
VIH		Vdd + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	ºC
Maximum Junction Temperature		130	ºC
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	ºC

Table 9. Thermal Considerations[7]

Package	θ_{JA}, 4 Layer Board (°C/W)	θ_{JC}, Bottom (°C/W)
3225, 6-pin	80	30
5032, 6-pin	53	20
7050, 6-pin	52	19

Notes:

7. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 10. Maximum Operating Junction Temperature[8]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C
95°C	120°C
105°C	130°C

Notes:

8. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 11. Environmental Compliance

Parameter	Test Conditions	Value	Unit
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	*g*
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	*g*
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C
Moisture Sensitivity Level	MSL1 @ 260°C		
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V
Charge-Device Model ESD Protection	JESD220C101	750	V
Latch-up Tolerance	JESD78 Compliant		

Waveform Diagrams

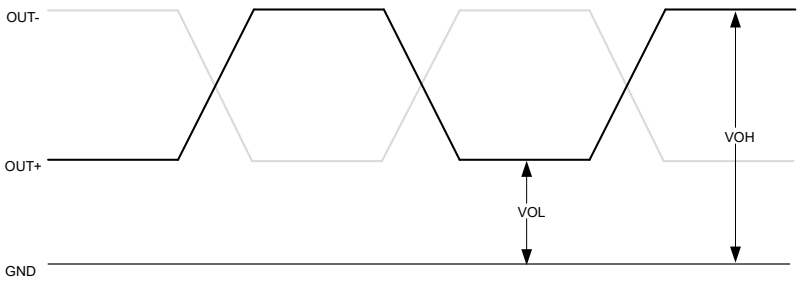


Figure 4. LVPECL, Low-swing LVPECL, and HCSL Voltage Levels per Differential Pin (i.e. OUT+, or OUT-)

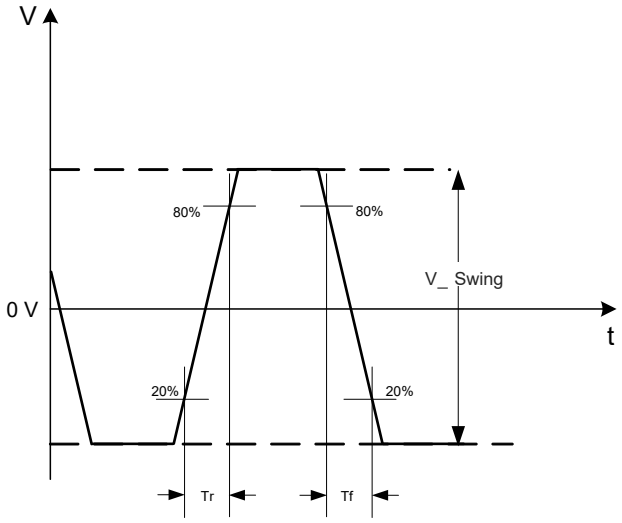


Figure 5. LVPECL, Low-swing LVPECL, and HCSL Voltage Levels Across Differential Pair (i.e. OUT+ minus OUT-)

Waveform Diagrams (continued)

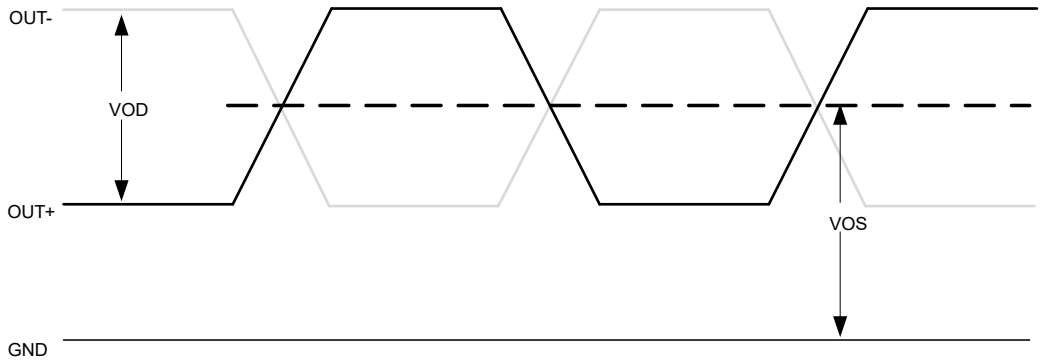


Figure 6. LVDS Voltage Levels per Differential Pin (i.e. OUT+, or OUT-)

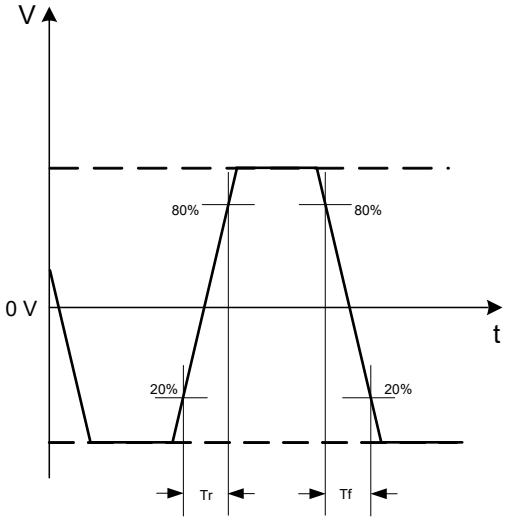


Figure 7. LVDS Differential Waveform (i.e. OUT+ minus OUT-)

Timing Diagrams

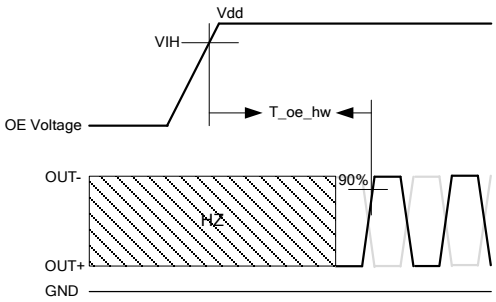


Figure 8. Hardware OE Enable Timing

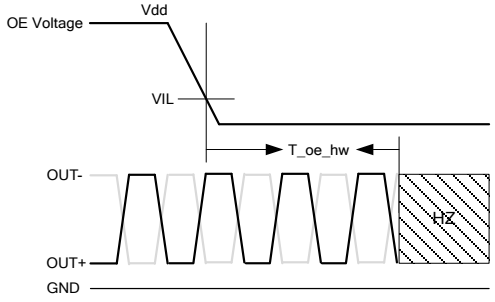


Figure 9. Hardware OE Disable Timing

Termination Diagrams

LVPECL and Low-swing LVPECL

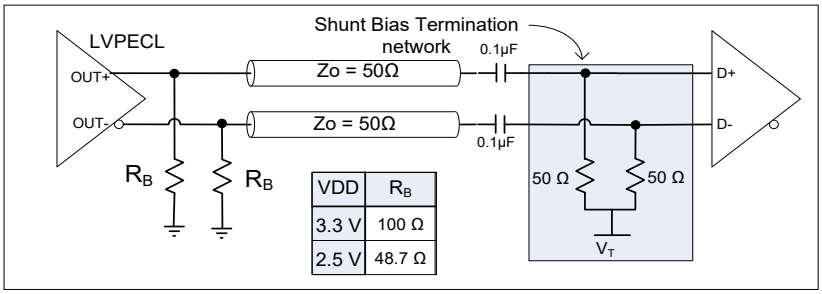


Figure 10. LVPECL and Low-swing LVPECL with AC-coupled Termination

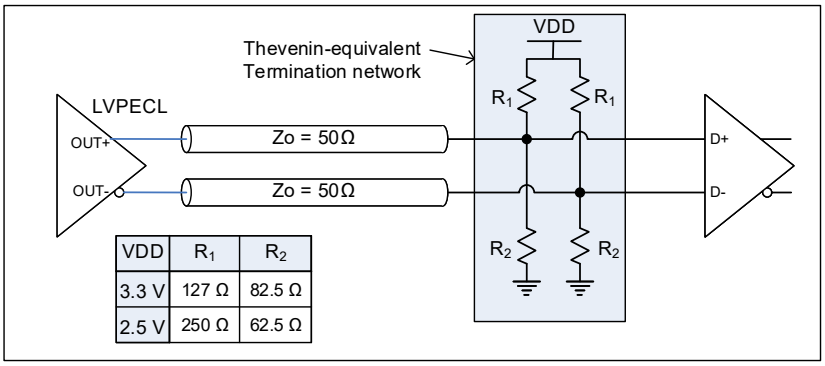


Figure 11. LVPECL and Low-swing LVPECL DC-coupled Load Termination with Thevenin Equivalent Network

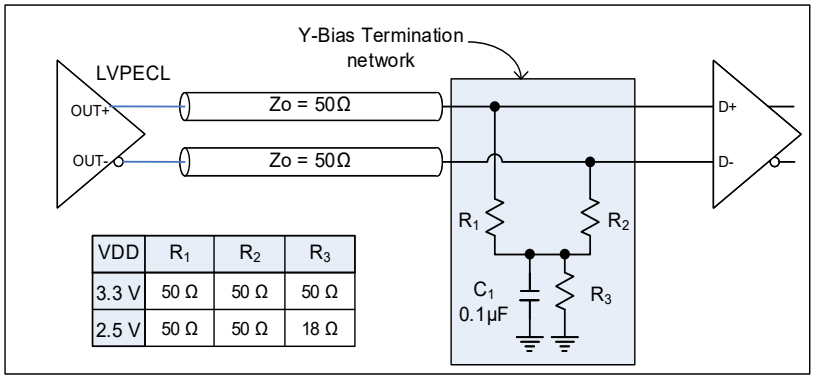


Figure 12. LVPECL and Low-swing LVPECL with Y-Bias Termination

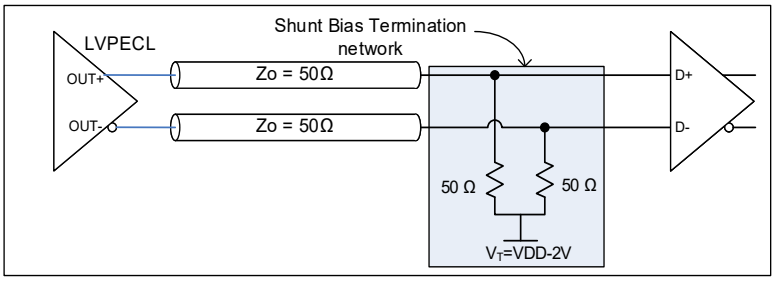


Figure 13. LVPECL and Low-swing LVPECL with DC-coupled Parallel Shunt Load Termination

Termination Diagrams (continued)

LVDS

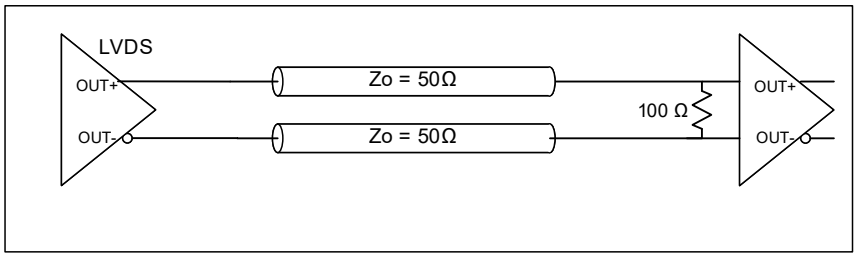


Figure 14. LVDS Single DC Termination at the Load

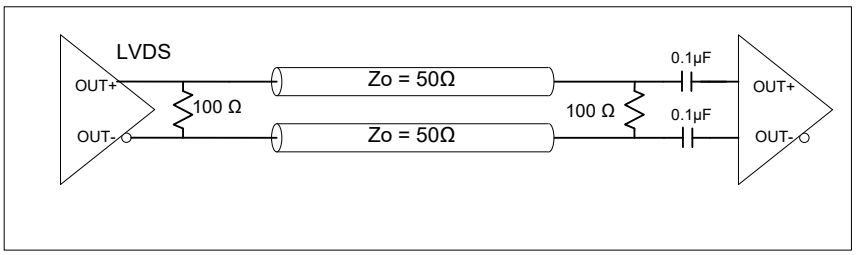


Figure 15. LVDS double AC Termination with Capacitor Close to the Load

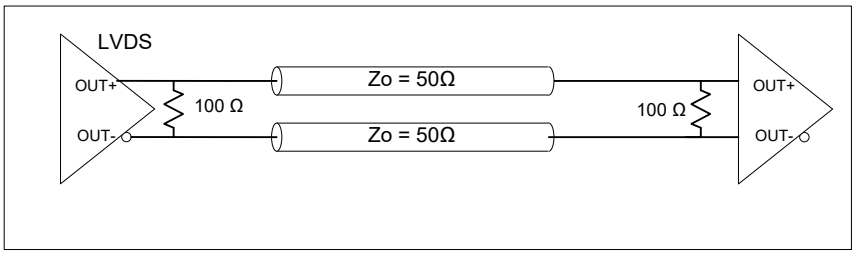


Figure 16. LVDS Double DC Termination

HCSL

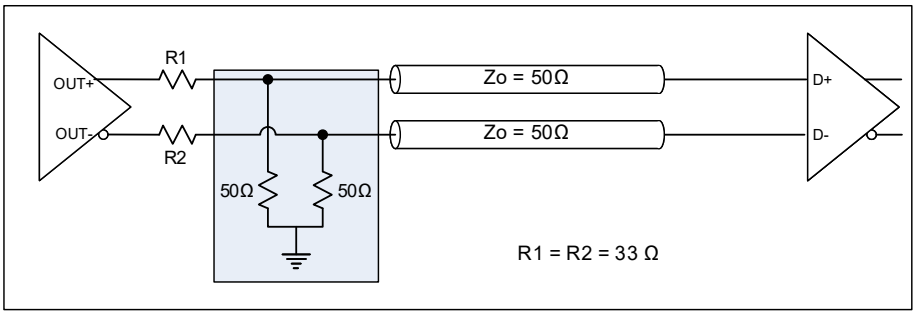
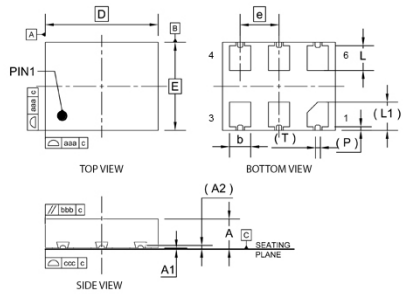


Figure 17. HCSL Interface Termination

Dimensions and Patterns — 3.2 x 2.5 mm²

Package Size – Dimensions (Unit: mm)[9]	Recommended Land Pattern (Unit: mm)[10]

3.2 x 2.5 x 0.85 mm

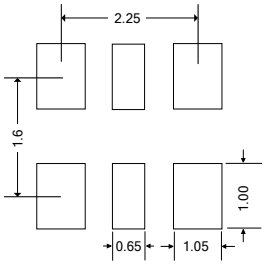


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.800	0.850	0.900
STAND OFF		A1	0.000	0.035	0.050
BODY SIZE	X	D		3.200 BSC	
	Y	E		2.500 BSC	
LEAD WIDTH		b	0.550	0.600	0.650
LEAD LENGTH		L	0.650	0.700	0.750
		L1		0.800 REF	
LEAD PITCH		e		1.100 BSC	
PACKAGE TOLERNCE		aaa		0.100	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	
DIMPLE WIDTH		T		0.150 REF	
DIMPLE LENGTH		P		0.150 REF	
DIMPLE DEPTH		A2		0.100 REF	

Notes
1. All dimensions are in millimeters

Package Outline	
6L PQFD	POD-038-PQFD-006-C03225
3.200x2.500x0.850 mm	SiTime
2021/07/15 Rev C00	

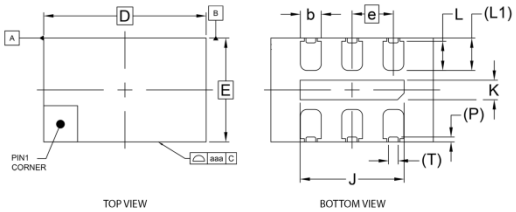
3.2 x 2.5 x 0.85 mm



Dimensions and Patterns — 5.0 x 3.2 mm²

Package Size – Dimensions (Unit: mm)[9]	Recommended Land Pattern (Unit: mm)[10]

5.0 x 3.2 x 0.85 mm[11]

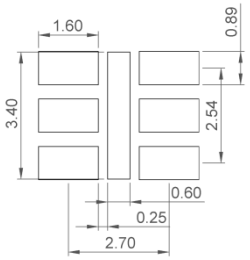


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.800	0.850	0.900
STAND OFF		A1	0.000	0.035	0.050
BODY SIZE	X	D		5.000 BSC	
	Y	E		3.200 BSC	
EP SIZE	X	J	3.100	3.200	3.300
	Y	K	0.500	0.600	0.700
LEAD WIDTH		b	0.590	0.640	0.690
LEAD LENGTH		L	0.850	0.900	0.950
		L1		1.000 REF	
LEAD PITCH		e		1.270 BSC	
PACKAGE TOLERANCE		aaa		0.100	
MOLD FLATNESS		bbb		0.100	
COPLANRITY		ccc		0.080	
DIMPLE WIDTH		T		0.300 REF	
DIMPLE LENGTH		P		0.150 REF	
DIMPLE DEPTH		A2		0.100 REF	

Notes
1. Dimensioning and tolerancing conform to ASME Y14.5-2009
2. All dimensions are in millimeters

Package Outline	
6L PQFV	POD-PQFV-006-C05032-039
5.000x3.200x0.850 mm	SiTime
2019/03/13 Rev B00	

5.0 x 3.2 x 0.85 mm[11]



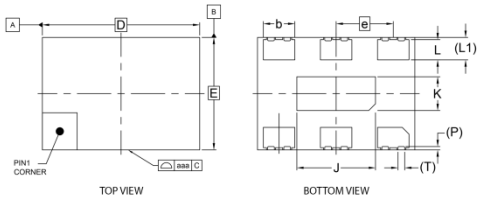
Notes:

9. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of “Y” will depend on the assembly location of the device.
10. A capacitor of value 0.1 µF or higher between VDD and GND is required. An additional 10 µF capacitor between VDD and GND is required for the best phase jitter performance.
11. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.

Dimensions and Patterns — 7.0 x 5.0 mm²

Package Size – Dimensions (Unit: mm)[12]	Recommended Land Pattern (Unit: mm)[13]

7.0 x 5.0 x 0.85 mm[14]

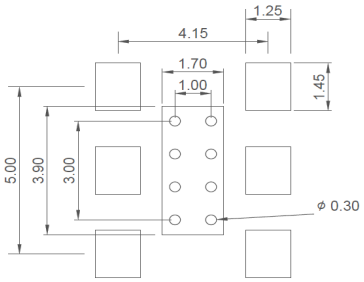


		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.800	0.850	0.900
STAND OFF		A1	0.000	0.035	0.050
BODY SIZE	X	D		7.000 BSC	
	Y	E		5.000 BSC	
EP SIZE	X	J	3.400	3.500	3.600
	Y	K	1.400	1.500	1.600
LEAD WIDTH		b	1.350	1.400	1.450
LEAD LENGTH		L	0.850	0.900	0.950
		L1		1.000 REF	
LEAD PITCH		e		2.540 BSC	
PACKAGE TOLERANCE		aaa		0.100	
MOLD FLATNESS		bbb		0.100	
COPLANRITY		ccc		0.080	
DIMPLE WIDTH		T		0.300 REF	
DIMPLE LENGTH		P		0.150 REF	
DIMPLE DEPTH		A2		0.100 REF	

Notes
1. Dimensioning and tolerancing conform to ASME Y14.5-2009
2. All dimensions are in millimeters

Package Outline	
6L PQFV	POD-PQFV-006-C07050-037
7.000x5.000x0.850 mm	SiTime
2019/03/13 Rev B00	

7.0 x 5.0 x 0.85 mm[14]



Note:
Circles in center pad are thermal vias, recommended to improve thermal performance

Notes:

12. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
13. A capacitor of value 0.1 µF or higher between VDD and GND is required. An additional 10 µF capacitor between VDD and GND is required for the best phase jitter performance.
14. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.

Additional Information

Table 12. Additional Information

Document	Description	Download Link
ECCN #: EAR99	Five character designation used on the commerce Control List (CCL) to identify dual use items for export control purposes.	—
HTS Classification Code: 8542.39.0000	A Harmonized Tariff Schedule (HTS) code developed by the World Customs Organization to classify/define internationally traded goods.	—
Part number Generator	Tool used to create the part number based on desired features.	https://www.sitime.com/part-number-generator
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	https://www.sitime.com/sites/default/files/gated/Manufacturing-Notes-for-SiTime-Products.pdf
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes
Evaluation Boards	SiT6085/6EB rev. 3.0, SiT6085EB rev.3.1 and SiT6097EB rev. 2.0 Evaluation Boards for Differential Oscillators User Manual	https://www.sitime.com/support/user-guides

Revision History

Table 13. Revision History

Revision	Release Date	Change Summary
1.0	6-Sep-2017	Final release
1.04	17-Apr-2018	Added 5032 package Added -40 to 95°C and -40 to 105°C temperature ranges Corrected minor errors| Added Additional Information Table
1.05	3-Jul-2018	Performed minor edits and updated Ordering Information
1.06	25-Oct-2018	Removed “Contact SiTime” for ±10 ppm
1.07	30-Jul-2019	Updated package Dimensions Drawings Updated Table 9 Thermal Considerations for 5032 package Updated Table 3 specification for First Year Aging Added 5, 10, and 20 year aging specs Added Evaluation Boards SiT6085EB reference in Table 12 Rearranged layout, added Description, Block Diagram and TOC Tightened LVDS minimum VOD specification Added HTS code Added low-swing LVPECL package code and specifications
1.08	17-Aug-2019	Formatting changes
1.09	9-Mar-2021	Updated L1 and Dimple Width package dimensions for 3.2 x 2.5 mm package Updated trademarks, hyperlinks and changed rev table date format
1.1	20-Jul-2021	Updated pin direction in package dimensions for 3.2 x 2.5 mm package

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Mouser Electronics

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SiTime:

SiT9365AC-2B2-33E50.000000G SiT9365AC-2E2-25E156.250000X SiT9365AC-1B2-33E125.000000G SiT9365AC-4E2-25E156.250000X SiT9365AC-4B2-33E100.000000G SiT9365AC-2B2-33E212.500000G SiT9365AC-2E2-33E156.250000X SiT9365AC-2B2-25E50.000000G SiT9365AC-4B2-25E156.250000G SiT9365AC-2B2-25E100.000000G SiT9365AC-2B2-33E156.250000G SiT9365AC-1E2-25E156.250000X SiT9365AC-4E2-33E156.250000X SiT9365AC-1E2-33E156.250000X SiT9365AC-1B2-33E100.000000G SiT9365AC-2B2-25E156.250000G SiT9365AC-2B2-33E100.000000G SiT9365AC-1B2-33E156.250000G SiT9365AC-1B2-33E156.253906G SiT9365AC-2E2-33E322.265600X SiT9365AC-2B1-33E125.000000G SiT9365AC-1B2-25E156.250000G SiT9365AC-1E2-33E156.253906X SiT9365AC-4B2-33E156.250000G SiT9365AC-2B2-25E322.265600G SiT9366AC-2B2-33E312.500000G SiT9367AC-2B2-33E285.000000G SiT9367AC-2B2-25E622.080000G SiT9367AC-2B2-25E500.000000G SiT9367AC-2B2-25E644.531250G SiT9367AC-2E2-33E622.080000X SiT9367AC-2B2-33E312.500000G SIT9365AI-4B3-33E25.000000G SiT9365AC-1E3-33E125.000000Y SiT9365AI-1E3-33E100.000000T SiT9365AI-2B2-33E125.000000T SiT9365AI-1B1-33E156.250000X SiT9365AI-1E3-33E100.000000Y SiT9365AI-2B3-25E250.000000Y SiT9365AC-2E2-33E322.265625X SiT9365AI-2B3-25E156.250000X SiT9365AI-4E1-33E100.000000X SiT9365AI-2B2-33E322.265625Y SiT9365AI-2B3-25E156.250000T SiT9365AC-4B1-33E100.000000T SiT9365AI-1E2-30E300.000000T SIT9365AI-4B3-25E100.000000Y SiT9365AI-1E3-33E100.000000X SiT9365AI-2B3-25E250.000000X SiT9365AI-2B3-33E100.000000Y SiT9365AI-2B3-33E156.250000T SiT9365AI-1B2-33E25.000000T SiT9365AI-2B3-33E250.000000Y SiT9365AI-2B3-33E250.000000T SiT9365AI-2B3-33E100.000000T SiT9365AI-2B2-33E322.265625T SiT9365AI-4B3-25E100.000000T